

MOSFETs Silicon N-Channel MOS

SSM3K72CTC

1. Applications

· High-Speed Switching

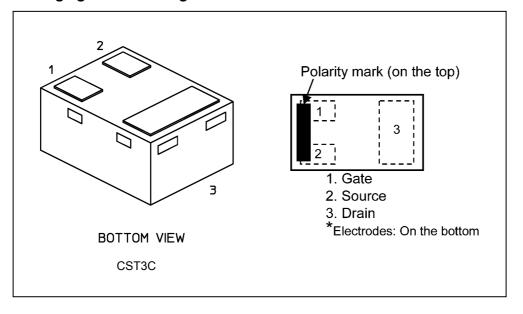
2. Features

- (1) ESD protected gate
- (2) Low drain-source on-resistance
 - : $R_{DS(ON)} = 2.8 \Omega \text{ (typ.) } (@V_{GS} = 10 \text{ V})$

 $\rm R_{DS(ON)} = 3.1~\Omega$ (typ.) (@V_{GS} = 5.0 V)

 $R_{\mathrm{DS(ON)}} = 3.2~\Omega~\mathrm{(typ.)}~(@V_{\mathrm{GS}} = 4.5~\mathrm{V})$

3. Packaging and Pin Assignment



Start of commercial production



4. Absolute Maximum Ratings (Note) (Unless otherwise specified, Ta = 25 °C)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	60	V
Gate-source voltage		V_{GSS}	±20	
Drain current (DC)	(Note 1)	I_D	150	mA
Drain current (pulsed)	(Note 1), (Note 2)	I _{DP}	600	
Power dissipation	(Note 3)	P_{D}	500	mW
Channel temperature		T _{ch}	150	°C
Storage temperature		T _{stg}	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

- Note 1: Ensure that the channel temperature does not exceed 150 °C.
- Note 2: Repetitive rating; pulse width limited by maximum channel temperature. pulse width \leq 10 $\mu s,$ Duty \leq 1 %
- Note 3: Device mounted on a 25.4 mm × 25.4 mm × 1.6 mm FR-4 glass epoxy board (Cu pad: 645 mm²)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

Note: The MOSFETs in this device are sensitive to electrostatic discharge. When handling this device, the worktables, operators, soldering irons and other objects should be protected against anti-static discharge.

Note: The channel-to-ambient thermal resistance, R_{th(ch-a)}, and the drain power dissipation, P_D, vary according to the board material, board area, board thickness and pad area. When using this device, be sure to take heat dissipation fully into account.



5. Electrical Characteristics

5.1. Static Characteristics (Unless otherwise specified, T_a = 25 °C)

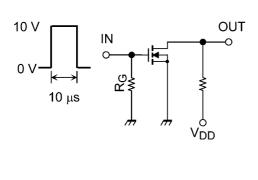
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±2	μА
		V_{GS} = ±10 V, V_{DS} = 0 V	_	_	±0.5	
		$V_{GS} = \pm 5 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±0.1	
Drain cut-off current	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V	_	_	1	μА
		$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V},$ $T_{ch} = 150 ^{\circ}\text{C}$	_	_	200	
Drain-source breakdown voltage	V _{(BR)DSS}	$I_D = 250 \mu A, V_{GS} = 0 V$	60	_	_	V
Gate threshold voltage	V _{th}	$I_D = 250 \mu A, V_{DS} = V_{GS}$	1.1	_	2.1	
Drain-source on-resistance (Note	1) R _{DS(ON)}	I _D = 100 mA, V _{GS} = 10 V	_	2.8	3.9	Ω
		I_D = 100 mA, V_{GS} = 10 V, T_{ch} = 150 °C	_	5.4	8.1	
		I _D = 100 mA, V _{GS} = 5.0 V	_	3.1	4.4	
		I _D = 100 mA, V _{GS} = 4.5 V	_	3.2	4.7	
		I _D = 5 mA, V _{GS} = 2.5 V	_	5.7	_	
Forward transfer admittance (Note	1) Y _{fs}	V _{DS} = 10 V, I _D = 200 mA	_	450	_	mS

Note 1: Pulse measurement.

5.2. Dynamic Characteristics (Unless otherwise specified, T_a = 25 °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 10 V, V _{GS} = 0 V,	_	11	17	pF
Reverse transfer capacitance	C _{rss}	f = 1 MHz	_	0.7	_	
Output capacitance	Coss		_	3	_	
Switching time (rise time)	t _r	V _{DD} = 40 V, I _D = 160 mA	_	3	_	ns
Switching time (turn-on delay time)	t _{d(on)}	V_{GS} = 0 to 10 V, R_G = 50 Ω Duty \leq 1 %, V_{IN} : t_r , t_f $<$ 5 ns, Common source, See Chapter 5.3.		2	4	
Switching time (fall time)	t _f			24	_	
Switching time (turn-off delay time)	t _{d(off)}	·	_	7	14	

5.3. Switching Time Test Circuit



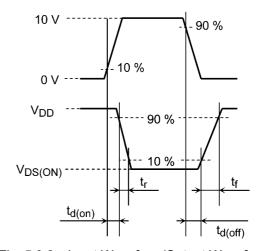


Fig. 5.3.1 Switching Time Test Circuit

Fig. 5.3.2 Input Waveform/Output Waveform



5.4. Gate Charge Characteristics (Unless otherwise specified, Ta = 25 °C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} = 30 \text{ V}, V_{GS} = 4.5 \text{ V},$	_	0.27	0.35	nC
Gate-source charge	Q _{gs}	I _D = 200 mA	_	80.0		
Gate-drain charge	Q _{gd}		_	0.08		

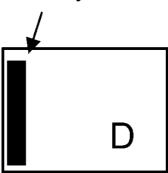
5.5. Source-Drain Characteristics (Unless otherwise specified, T_a = 25 °C)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	(Note 1)	V_{DSF}	$I_D = -115 \text{ mA}, V_{GS} = 0 \text{ V}$		0.87	-1.2	V

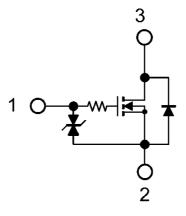
Note 1: Pulse measurement.

6. Marking

Polarity mark



7. Equivalent Circuit





8. Characteristics Curves (Note)

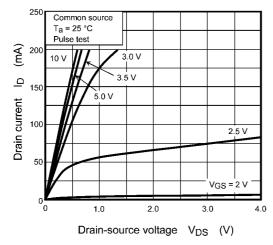


Fig. 8.1 I_D - V_{DS}

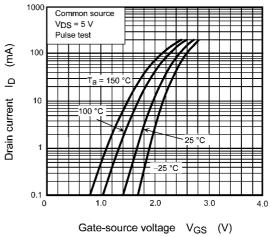


Fig. 8.2 I_D - V_{GS}

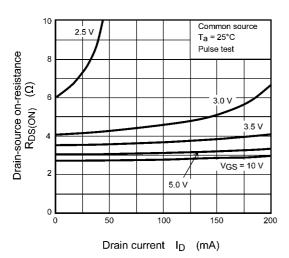


Fig. 8.3 R_{DS(ON)} - I_D

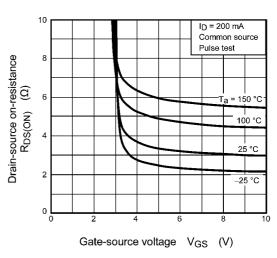


Fig. 8.4 R_{DS(ON)} - V_{GS}

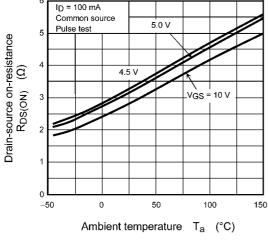


Fig. 8.5 R_{DS(ON)} - T_a

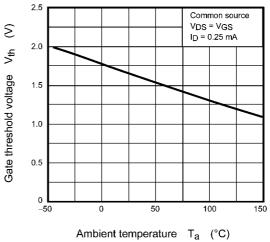
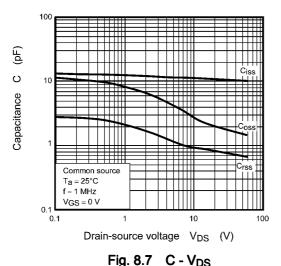
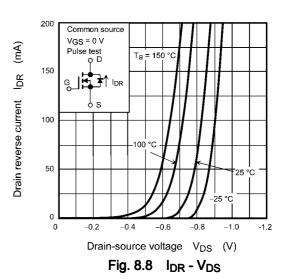


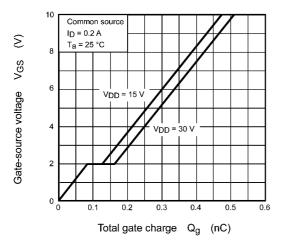
Fig. 8.6 V_{th} - T_a

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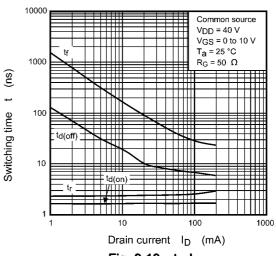
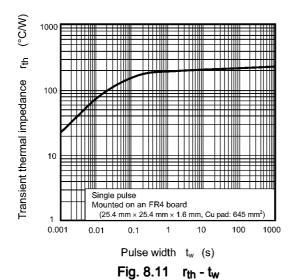


Fig. 8.9 Dynamic Input Characteristics





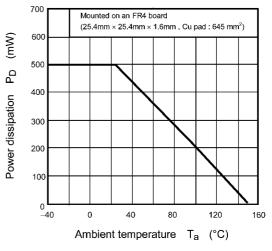


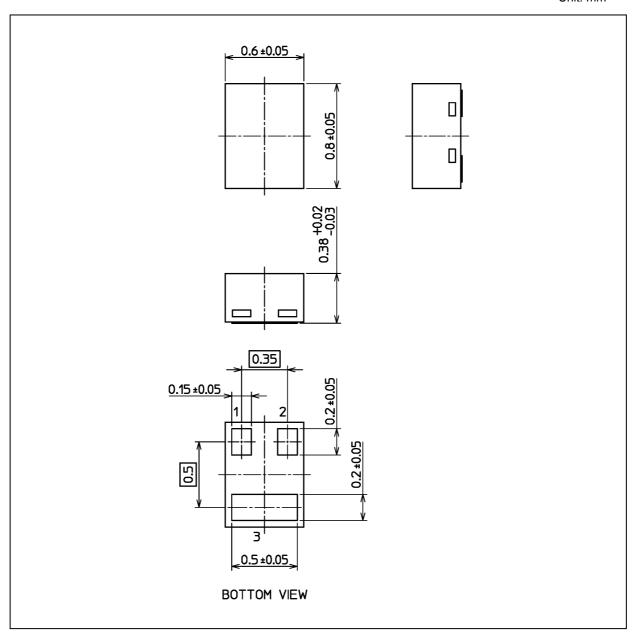
Fig. 8.12 P_D - T_a

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 0.55 mg (typ.)

Package Name(s)
Nickname: CST3C



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